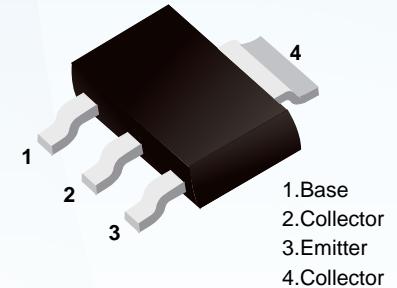


■ PNP Transistors

■ Features

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage
- Complementary to BCP54, BCP55, BCP56

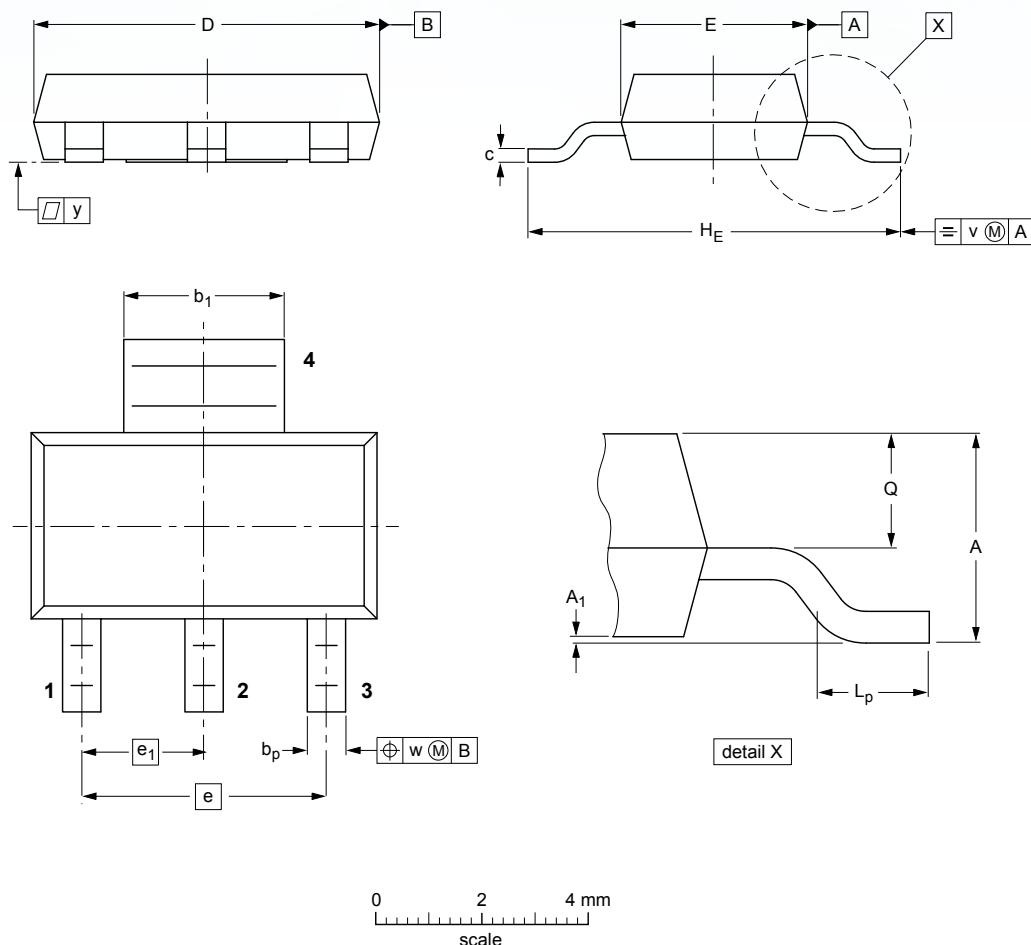
■ Simplified outline(SOT-223)
■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	BCP51	BCP52	BCP53	Unit
Collector - Base Voltage	V _{CBO}	-45	-60	-100	V
Collector - Emitter Voltage	V _{CEO}	-45	-60	-80	
Emitter - Base Voltage	V _{EBO}		-5		
Collector Current - Continuous	I _C		-1		A
Collector Power Dissipation	P _C		1.5		W
Thermal Resistance Junction to Ambient	R _{θJA}		94		°C/W
Junction Temperature	T _J		150		°C
Storage Temperature Range	T _{stg}		-65 to 150		

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	$I_c = -100 \mu\text{A}, I_E = 0$	-45			V
			-60			
			-100			
Collector- emitter breakdown voltage	V _{CEO}	$I_c = -10 \text{ mA}, I_B = 0$	-45			V
			-60			
			-80			
Emitter - base breakdown voltage	V _{EBO}	$I_E = -100 \mu\text{A}, I_c = 0$	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -45 V , $I_E = 0$				uA
		V _{CB} = -60 V , $I_E = 0$				
		V _{CB} = -100 V , $I_E = 0$				
Emitter cut-off current	I _{EBO}	V _{EB} = -5V , $I_c = 0$				-0.1
Collector-emitter saturation voltage	V _{CE(sat)}	$I_c = -500 \text{ mA}, I_B = -50 \text{ mA}$				-0.5
Base - emitter saturation voltage	V _{BE(sat)}	$I_c = -500 \text{ mA}, I_B = -50 \text{ mA}$				-1.2
Base-emitter voltage	V _{BE}	V _{CE} = -2V, $I_c = -500 \text{ mA}$				-1
DC current gain	$h_{FE}(1)$	V _{CE} = -2V, $I_c = -5 \text{ mA}$	25			
	$h_{FE}(2)$	V _{CE} = -2V, $I_c = -150 \text{ mA}$	63		250	
	$h_{FE}(3)$	V _{CE} = -2V, $I_c = -500 \text{ mA}$	25			
Transition frequency	f _T	V _{CE} = -10V, $I_c = -50 \text{ mA}, f = 100 \text{ MHz}$	100			MHz

■ SOT-223



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.8 1.5	0.10 0.01	0.80 0.60	3.1 2.9	0.32 0.22	6.7 6.3	3.7 3.3	4.6	2.3	7.3 6.7	1.1 0.7	0.95 0.85	0.2	0.1	0.1

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